74HC574; 74HCT574

Octal D-type flip-flop; positive edge-trigger; 3-state

Rev. 6 — 26 January 2015

Production

Product data sheet

General description 1.

The 74HC574; 74HCT574 is a high-speed Si-gate CMOS device and is pin compatible with Low-power Schottky TTL. It is specified in compliance with JEDEC standard no. 7A.

The 74HC574; 74HCT574 are octal D-type flip-flops featuring separate D-type inputs for each flip-flop and 3-state outputs for bus-oriented applications. A clock (CP) and an output enable (OE) input are common to all flip-flops. The 8 flip-flops will store the state of their individual D-inputs that meet the set-up and hold times requirements on the LOW-to-HIGH CP transition. When \overline{OE} is LOW the contents of the 8 flip-flops are available at the outputs. When OE is HIGH, the outputs go to the high-impedance OFF-state. Operation of the OE input does not affect the state of the flip-flops.

The 74HC574; 74HCT574 is functionally identical to:

- 74HC564: but has non-inverting outputs
- 74HC374; 74HCT374: but has a different pin arrangement

Features and benefits 2.

- 3-state non-inverting outputs for bus oriented applications
- 8-bit positive, edge-triggered register
- Common 3-state output enable input
- ESD protection:
 - ♦ HBM JESD22-A114F exceeds 2 000 V
 - MM JESD22-A115-A exceeds 200 V
- Specified from -40 °C to +85 °C and from -40 °C to +125 °C

Ordering information

Table 1. **Ordering information**

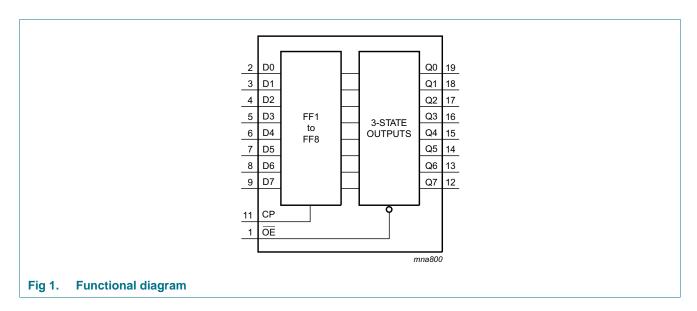
Type number	Package									
	Temperature range	Name	Description	Version						
74HC574N	−40 °C to +125 °C	DIP20	plastic dual in-line package; 20 leads (300 mil)	SOT146-1						
74HCT574N	-									
74HC574D	–40 °C to +125 °C	SO20	plastic small outline package; 20 leads;	SOT163-1						
74HCT574D			body width 7.5 mm							

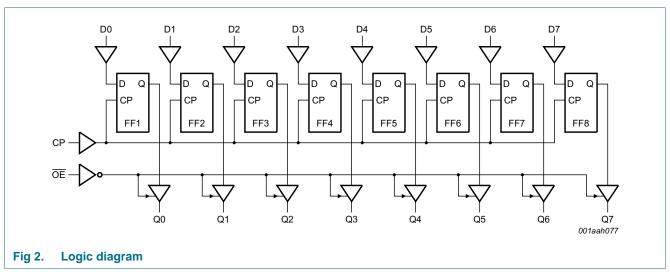


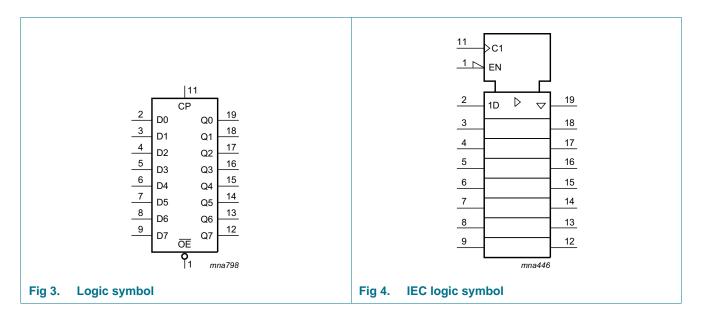
 Table 1.
 Ordering information ...continued

Type number	Package									
	Temperature range	Name	Description	Version						
74HC574DB	−40 °C to +125 °C	SSOP20	plastic shrink small outline package; 20 leads;	SOT339-1						
74HCT574DB			body width 5.3 mm							
74HC574PW	−40 °C to +125 °C	TSSOP20	plastic thin shrink small outline package; 20 leads;	SOT360-1						
74HCT574PW	-		body width 4.4 mm							

4. Functional diagram

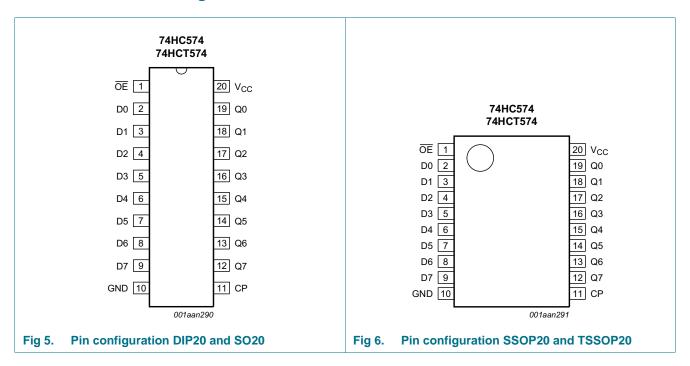






5. Pinning information

5.1 Pinning



5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
OE	1	3-state output enable input (active LOW)
D[0:7]	2, 3, 4, 5, 6, 7, 8, 9	data input
GND	10	ground (0 V)
СР	11	clock input (LOW-to-HIGH, edge triggered)
Q[0:7]	19, 18, 17, 16, 15, 14, 13, 12	3-state flip-flop output
V _{CC}	20	supply voltage

6. Functional description

Table 3. Function table[1]

Operating mode	Input		Internal	Output	
	OE	СР	Dn	flip-flop	Qn
Load and read register	L	↑	I	L	L
	L	↑	h	Н	Н
Load register and disable output	Н	↑	I	L	Z
	Н	↑	h	Н	Z

^[1] H = HIGH voltage level;

h = HIGH voltage level one setup time prior to the HIGH-to-LOW CP transition;

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CC}	supply voltage			-0.5	+7	V
I _{IK}	input clamping current	$V_{I} < -0.5 \text{ V or } V_{I} > V_{CC} + 0.5 \text{ V}$		-	±20	mA
I _{OK}	output clamping current	$V_O < -0.5 \text{ V or } V_O > V_{CC} + 0.5 \text{ V}$		-	±20	mA
I _O	output current	$V_{O} = -0.5 \text{ V to } (V_{CC} + 0.5 \text{ V})$		-	±35	mA
I _{CC}	supply current			-	+70	mA
I_{GND}	ground current			-	-70	mA
T _{stg}	storage temperature			-65	+150	°C
P _{tot}	total power dissipation	DIP20 package	[1]	-	750	mW
		SO20, SSOP20 and TSSOP20 packages	[2]	-	500	mW

^[1] For DIP20 package: P_{tot} derates linearly with 12 mW/K above 70 °C.

74HC_HCT574

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L = LOW voltage level;

I = LOW voltage level one setup time prior to the HIGH-to-LOW CP transition;

Z = high-impedance OFF-state;

 $[\]uparrow$ = LOW-to-HIGH clock transition.

^[2] For SO20: P_{tot} derates linearly with 8 mW/K above 70 °C. For SSOP20 and TSSOP20 packages: P_{tot} derates linearly with 5.5 mW/K above 60 °C.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V)

Symbol	Parameter	Conditions	74HC574			7	4	Unit	
			Min	Тур	Max	Min	Тур	Max	
V _{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
VI	input voltage		0	-	V _{CC}	0	-	V _{CC}	V
Vo	output voltage		0	-	V _{CC}	0	-	V _{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C
Δt/ΔV	input transition rise and fall rate	V _{CC} = 2.0 V	-	-	625	-	-	-	ns/V
		V _{CC} = 4.5 V	-	1.67	139	-	1.67	139	ns/V
		V _{CC} = 6.0 V	-	-	83	-	-	-	ns/V

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		-40 °C t	o +85 °C	-40 °C to	o +125 °C	Unit
			Min	Тур	Max	Min	Max	Min	Max	
74HC574	4							1		
V _{IH}	HIGH-level	V _{CC} = 2.0 V	1.5	1.2	-	1.5	-	1.5	-	V
	input voltage	V _{CC} = 4.5 V	3.15	2.4	-	3.15	-	3.15	-	V
		V _{CC} = 6.0 V	4.2	3.2	-	4.2	-	4.2	-	V
V_{IL}	LOW-level	V _{CC} = 2.0 V	-	0.8	0.5	-	0.5	-	0.5	V
	input voltage	V _{CC} = 4.5 V	-	2.1	1.35	-	1.35	-	1.35	V
		V _{CC} = 6.0 V	-	2.8	1.8	-	1.8	-	1.8	V
V _{OH}	HIGH-level	$V_I = V_{IH}$ or V_{IL}								
	output voltage	$I_O = -20 \mu A; V_{CC} = 2.0 V$	1.9	2.0	-	1.9	-	1.9	-	V
		$I_O = -20 \mu A; V_{CC} = 4.5 V$	4.4	4.5	-	4.4	-	4.4	-	V
		$I_O = -20 \mu A; V_{CC} = 6.0 V$	5.9	6.0	-	5.9	-	5.9	-	V
		$I_{O} = -6.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.98	4.32	-	3.84	-	3.7	-	V
		$I_{O} = -7.8 \text{ mA}; V_{CC} = 6.0 \text{ V}$	5.48	5.81	-	5.34	-	5.2	-	V
V _{OL}	LOW-level	$V_I = V_{IH}$ or V_{IL}								
	output voltage	$I_O = 20 \mu A; V_{CC} = 2.0 V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 20 \mu A; V_{CC} = 4.5 V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 20 \mu A; V_{CC} = 6.0 \text{ V}$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 6.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	0.15	0.26	-	0.33	-	0.4	V
		$I_O = 7.8 \text{ mA}; V_{CC} = 6.0 \text{ V}$	-	0.16	0.26	-	0.33	-	0.4	V
I _I	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 6.0 \text{ V}$	-	-	±0.1	-	±1.0	-	±1.0	μА
l _{OZ}	OFF-state $V_{CC} = 0.0 \text{ V}$ output current $V_{I} = V_{IH} \text{ or } V_{IL};$ $V_{O} = V_{CC} \text{ or GND};$ $V_{CC} = 6.0 \text{ V}$		-	-	±0.5	-	±5.0	-	±10.0	μА

 Table 6.
 Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		-40 °C t	o +85 °C	-40 °C to +125 °C		Unit
			Min	Тур	Max	Min	Max	Min	Max	
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 6.0 \text{ V}$	-	-	8.0	-	80	-	160	μΑ
C _I	input capacitance		-	3.5	-					pF
74HCT5	74		1		1					
V _{IH}	HIGH-level input voltage	V _{CC} = 4.5 V to 5.5 V	2.0	1.6	-	2.0	-	2.0	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 4.5 V to 5.5 V	-	1.2	0.8	-	0.8	-	0.8	V
V _{OH}	HIGH-level	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5 \text{ V}$								
	output voltage	$I_{O} = -20 \mu A$	4.4	4.5	-	4.4	-	4.4	-	V
		$I_O = -6 \text{ mA}$	3.98	4.32	-	3.84	-	3.7	-	V
V _{OL}	LOW-level	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5 \text{ V}$								
	output voltage	I _O = 20 μA	-	0	0.1	-	0.1	-	0.1	V
		$I_{O} = 6.0 \text{ mA}$	-	0.16	0.26	-	0.33	-	0.4	V
I _I	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$	-	-	±0.1	-	±1.0	-	±1.0	μА
I _{OZ}	OFF-state output current	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 5.5$ V; $V_O = V_{CC}$ or GND per input pin; other inputs at V_{CC} or GND; $I_O = 0$ A	-	-	±0.5	-	±5.0	-	±10	μА
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5$ V	-	-	8.0	-	80	-	160	μΑ
Δl _{CC}	additional supply current	$\begin{aligned} &V_{I} = V_{CC} - 2.1 \text{ V;} \\ &\text{other inputs at } V_{CC} \text{ or GND;} \\ &V_{CC} = 4.5 \text{ V to } 5.5 \text{ V;} \\ &I_{O} = 0 \text{ A} \end{aligned}$								
		per input pin; Dn inputs	-	50	180	-	225	-	245	μΑ
		per input pin; OE input	-	125	450	-	563	-	613	μΑ
		per input pin; CP input	-	150	540	-	675	-	735	μΑ
Cı	input capacitance		-	3.5	-	-	-	-	-	pF

10. Dynamic characteristics

Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); C_L = 50 pF unless otherwise specified; for test circuit see Figure 10.

Symbol	Parameter	Conditions		25 °C		-40 °C	to +85 °C	-40 °C to +125 °C		Unit
			Mir	Тур	Max	Min	Max	Min	Max	
74HC57	4									
t _{pd}	propagation	CP to Qn; see Figure 7	[1]							
	delay	V _{CC} = 2.0 V	-	47	150	-	190	-	225	ns
		V _{CC} = 4.5 V	-	17	30	-	35	-	45	ns
		V _{CC} = 5 V; C _L = 15 pF	-	14	-	-	-	-	-	ns
		V _{CC} = 6.0 V	-	14	26	-	33	-	38	ns
t _{en}	enable time	OE to Qn; see Figure 9	[2]							
		V _{CC} = 2.0 V	-	44	140	-	175	-	210	ns
		V _{CC} = 4.5 V	-	16	28	-	35	-	42	ns
		V _{CC} = 6.0 V	-	13	24	-	30	-	36	ns
t _{dis}	disable time	OE to Qn; see Figure 9	[3]							
		V _{CC} = 2.0 V	-	39	125	-	155	-	190	ns
		V _{CC} = 4.5 V	-	14	25	-	31	-	38	ns
		V _{CC} = 6.0 V	-	11	21	-	26	-	32	ns
t _t	transition	Qn; see Figure 7	[4]							
	time	V _{CC} = 2.0 V	-	14	60	-	75	-	90	ns
		V _{CC} = 4.5 V	-	5	12	-	15	-	18	ns
		V _{CC} = 6.0 V	-	4	10	-	13	-	15	ns
t _W	pulse width	CP HIGH or LOW; see Figure 8								
		V _{CC} = 2.0 V	80	14	-	100	-	120	-	ns
		V _{CC} = 4.5 V	16	5	-	20	-	24	-	ns
		V _{CC} = 6.0 V	14	4	-	17	-	20	-	ns
t _{su}	set-up time	Dn to CP; see Figure 8								
		V _{CC} = 2.0 V	60	6	-	75	-	90	-	ns
		V _{CC} = 4.5 V	12	2	-	15	-	18	-	ns
		V _{CC} = 6.0 V	10	2	-	13	-	15	-	ns
t _h	hold time	Dn to CP; see Figure 8								
		V _{CC} = 2.0 V	5	0	-	5	-	5	-	ns
		V _{CC} = 4.5 V	5	0	-	5	-	5	-	ns
		V _{CC} = 6.0 V	5	0	-	5	-	5	-	ns
f _{max}	maximum	CP; see Figure 7								
	frequency	V _{CC} = 2.0 V	6.0	37	-	4.8	-	4.0	-	MHz
		V _{CC} = 4.5 V	30	112	-	24	-	20	-	MHz
		V _{CC} = 5 V; C _L = 15 pF	-	123	-	-	-	-	-	MHz
		V _{CC} = 6.0 V	35	133	-	28	-	24	-	MHz

 Table 7.
 Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); $C_L = 50 \text{ pF}$ unless otherwise specified; for test circuit see Figure 10.

Symbol	Parameter	Conditions			25 °C		-40 °C	to +85 °C	-40 °C 1	to +125 °C	Unit
				Min	Тур	Max	Min	Max	Min	Max	
C _{PD}	power dissipation capacitance	$C_L = 50 \text{ pF}; f = 1 \text{ MHz};$ $V_I = \text{GND to } V_{CC}$		-	22	-	-	-	-	-	pF
74HCT5	74										
t _{pd}	propagation	CP to Qn; see Figure 7	<u>[1]</u>								
	delay	V _{CC} = 4.5 V		-	18	33	-	41	-	50	ns
		$V_{CC} = 5 \text{ V}; C_L = 15 \text{ pF}$		-	15	-	-	-	-	-	ns
t _{en}	enable time	OE to Qn; see Figure 9	[2]								
		V _{CC} = 4.5 V		-	19	33	-	41	-	50	ns
t _{dis}	disable time	OE to Qn; see Figure 9	[3]								
		V _{CC} = 4.5 V		-	16	28	-	35	-	42	ns
t _t	transition	Qn; see Figure 7	[4]								
	time	V _{CC} = 4.5 V		-	5	12	-	15	-	18	ns
t _W	pulse width	CP HIGH or LOW; see Figure 8									
		V _{CC} = 4.5 V		16	7	-	20	-	24	-	ns
t _{su}	set-up time	Dn to CP; see Figure 8									
		V _{CC} = 4.5 V		12	3	-	15	-	18	-	ns
t _h	hold time	Dn to CP; see Figure 8									
		V _{CC} = 4.5 V		5	-1	-	5	-	5	-	ns
f _{max}	maximum	CP; see Figure 7									
	frequency	V _{CC} = 4.5 V		30	69	-	24	-	20	-	MHz
		$V_{CC} = 5 \text{ V}; C_L = 15 \text{ pF}$		-	76	-	-	-	-	-	MHz
C _{PD}	power dissipation capacitance	C_L = 50 pF; f = 1 MHz; V _I = GND to V _{CC} - 1.5 V	<u>[5]</u>	-	25	-	-	-	-	-	pF

- [1] t_{pd} is the same as t_{PLH} and t_{PHL} .
- [2] t_{en} is the same as t_{PZH} and t_{PZL} .
- [3] t_{dis} is the same as t_{PLZ} and t_{PHZ} .
- [4] t_t is the same as t_{THL} and t_{TLH} .
- [5] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum (C_L \times V_{CC}^2 \times f_o)$ where:

f_i = input frequency in MHz;

f_o = output frequency in MHz;

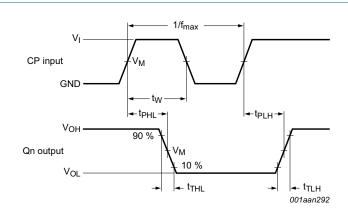
 C_L = output load capacitance in pF;

 V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\sum (C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

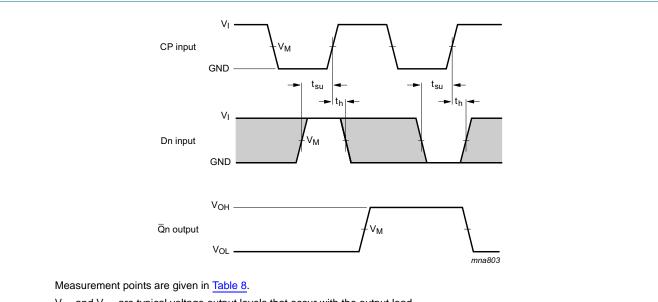
11. Waveforms



Measurement points are given in Table 8.

 V_{OL} and V_{OH} are typical voltage output levels that occur with the output load.

Fig 7. Propagation delay input (CP) to output (Qn), output transition time, clock input (CP) pulse width and the maximum frequency (CP)



 V_{OL} and V_{OH} are typical voltage output levels that occur with the output load.

Fig 8. The data input (D) to clock input (CP) set-up times and clock input (CP) to data input (D) hold times

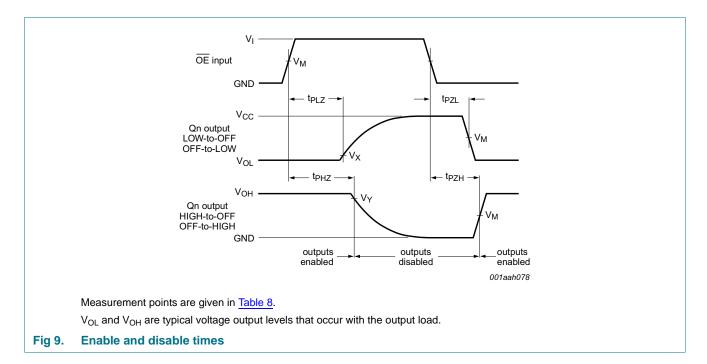
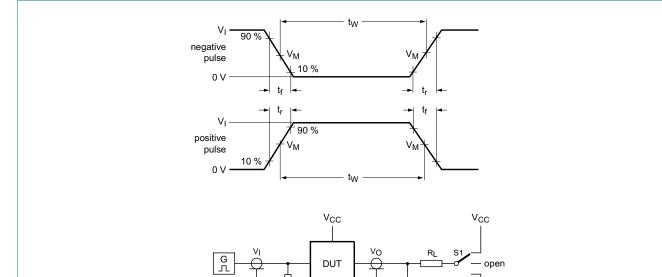


Table 8. Measurement points

Туре	Input	Output						
	V_{M}	V _M	V_X	V _Y				
74HC574	0.5V _{CC}	0.5V _{CC}	0.1V _{CC}	0.9V _{CC}				
74HCT574	1.3 V	1.3 V	0.1V _{CC}	0.9V _{CC}				

001aad983



Test data is given in Table 9.

Definitions test circuit:

 R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

 C_L = Load capacitance including jig and probe capacitance.

 R_L = Load resistance.

S1 = Test selection switch.

Fig 10. Test circuit for measuring switching times

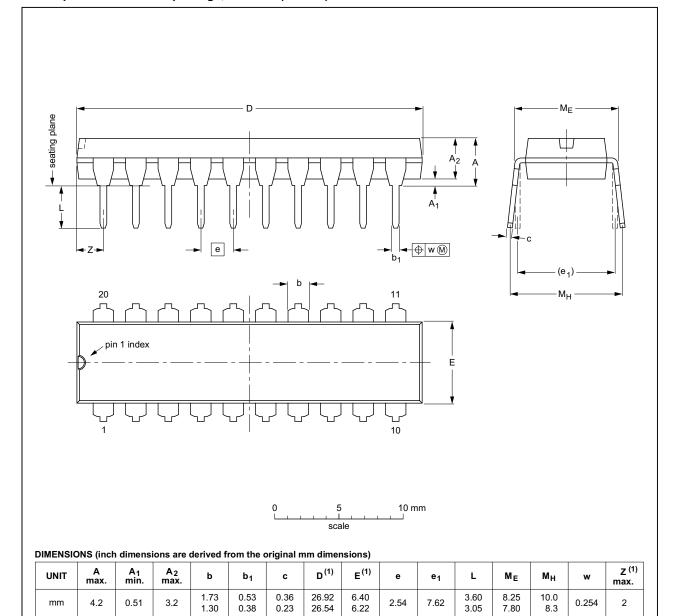
Table 9. Test data

Туре	Input		Load		S1 position			
	VI	t _r , t _f	CL	R _L	t _{PHL} , t _{PLH}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ}	
74HC574	V _{CC}	6 ns	15 pF, 50 pF	1 kΩ	open	GND	V _{CC}	
74HCT574	3 V	6 ns	15 pF, 50 pF	1 kΩ	open	GND	V _{CC}	

12. Package outline

DIP20: plastic dual in-line package; 20 leads (300 mil)

SOT146-1



Note

inches

0.17

1. Plastic or metal protrusions of 0.25 mm (0.01 inch) maximum per side are not included.

0.068

0.021

0.015

0.014

0.009

OUTLINE		REFER	ENCES		EUROPEAN	ISSUE DATE	
VERSION	IEC	IEC JEDEC JEITA		PROJECTION		ISSUE DATE	
SOT146-1		MS-001	SC-603			99-12-27 03-02-13	

1.060

0.25

0.14

0.3

0.32

0.39

0.01

0.078

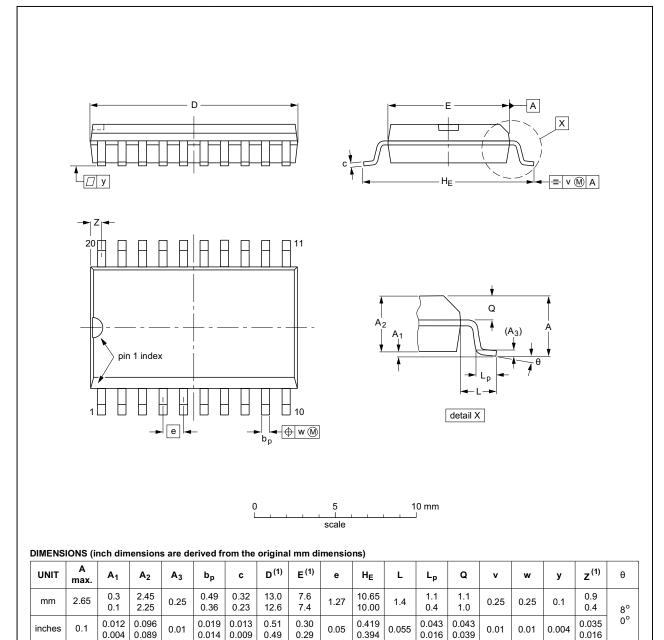
Fig 11. Package outline SOT146-1 (DIP20)

0.02

0.13

SO20: plastic small outline package; 20 leads; body width 7.5 mm

SOT163-1



Note

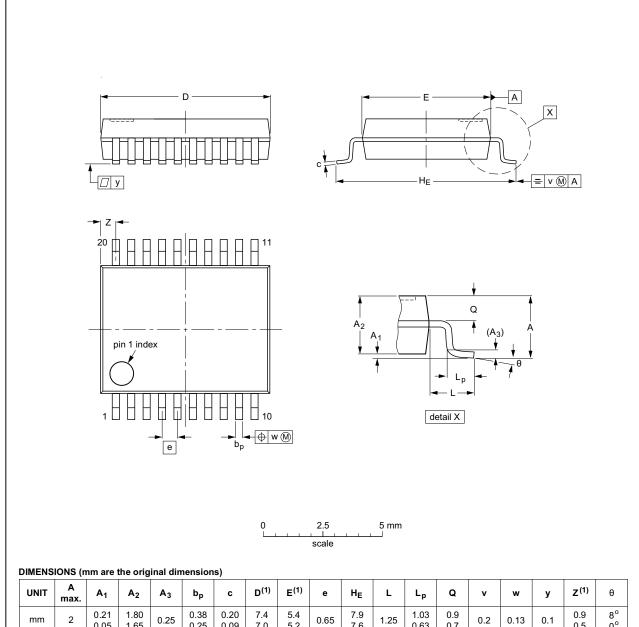
1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE		REFER	RENCES	EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA	PROJECTION	155UE DATE	
SOT163-1	075E04	MS-013			99-12-27 03-02-19	

Fig 12. Package outline SOT163-1 (SO20)

SSOP20: plastic shrink small outline package; 20 leads; body width 5.3 mm

SOT339-1



UNIT	A max.	A ₁	A ₂	A ₃	bp	С	D ⁽¹⁾	E ⁽¹⁾	е	HE	L	Lp	ø	v	¥	у	Z ⁽¹⁾	θ
mm	2	0.21 0.05	1.80 1.65	0.25	0.38 0.25	0.20 0.09	7.4 7.0	5.4 5.2	0.65	7.9 7.6	1.25	1.03 0.63	0.9 0.7	0.2	0.13	0.1	0.9 0.5	8° 0°

Note

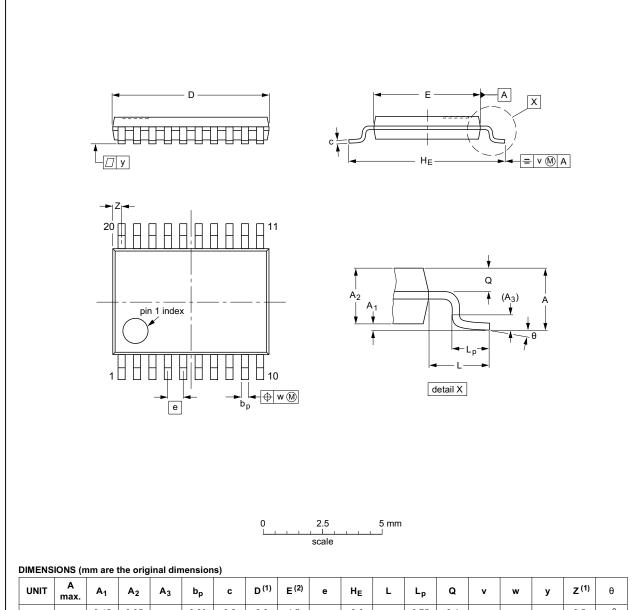
1. Plastic or metal protrusions of 0.2 mm maximum per side are not included.

OUTLINE		REFER	RENCES	EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE	
SOT339-1		MO-150			99-12-27 03-02-19	

Fig 13. Package outline SOT339-1 (SSOP20)

TSSOP20: plastic thin shrink small outline package; 20 leads; body width 4.4 mm

SOT360-1



	(Ψ,												
UNIT	A max.	A ₁	A ₂	A ₃	bp	С	D (1)	E (2)	е	HE	L	Lp	Q	v	w	у	Z ⁽¹⁾	θ
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	6.6 6.4	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.5 0.2	8° 0°

Notes

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC JEDEC	JEITA	PROJECTION	ISSUE DATE	
SOT360-1		MO-153			99-12-27 03-02-19

Fig 14. Package outline SOT360-1 (TSSOP20)

13. Abbreviations

Table 10. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

14. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT574 v.6	20150126	Product data sheet	-	74HC_HCT574 v.5
Modifications:	• <u>Table 7</u> : Po	wer dissipation capacitanc	e condition for 74HC	574 is corrected.
74HC_HCT574 v.5	20120425	Product data sheet	-	74HC_HCT574 v.4
Modifications:	 V_X and V_Y 	measurement points added	to Table 8.	
74HC_HCT574 v.4	20111219	Product data sheet	-	74HC_HCT574 v.3
Modifications:	Legal page	s updated.		
74HC_HCT574 v.3	20101215	Product data sheet	-	74HC_HCT574_CNV v.2
74HC_HCT574_CNV v.2	19970827	Product specification	-	-

15. Legal information

15.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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74HC_HCT574

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74HC574; 74HCT574

Octal D-type flip-flop; positive edge-trigger; 3-state

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